

55V / 110A
N-Channel Enhancement Mode MOSFET

55V, $R_{DS(ON)}=5.5m\Omega@V_{GS}=10V, I_D=30A$

Features

- Low On-State Resistance
- Excellent Gate Charge x $R_{DS(ON)}$ Product (FOM)
- Fully Characterized Avalanche Voltage and Current
- Specially Designed for DC-DC Converter, Off-line UPS, Automotive System, Solenoid and Motor Control
- In compliance with EU RoHs 2002/95/EC Directives

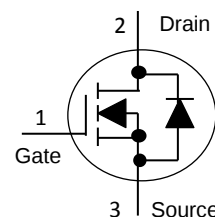
Mechanical Information

- Case: TO-220AB Molded Plastic
- Terminals : Solderable per MIL-STD-750,Method 2026

Marking & Ordering Information

TYPE	MARKING	PACKAGE	PACKING
HY110N06T	110N06T	TO-220AB	50PCS/TUBE

TO-220AB



Absolute Maximum Ratings ($T_c=25^\circ\text{C}$ unless otherwise specified)

Parameter		Symbol	Value	Units
Drain-Source Voltage		V_{DS}	55	V
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current ¹⁾	$T_c=25^\circ\text{C}$	I_D	110	A
Pulsed Drain Current ¹⁾		I_{DM}	420	A
Maximum Power Dissipation	$T_c=25^\circ\text{C}$	P_D	125	W
Derating Factor			0.83	
Avalanche Energy with Single Pulse, $L=0.3mH$		E_{AS}	470	mJ
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55 to +175	$^\circ\text{C}$

Note : 1. Maximum DC current limited by the package

Thermal Characteristics

Parameter	Symbol	Value	Units
Junction-to-Case Thermal Resistance	$R_{\theta JC}$	1.2	$^\circ\text{C/W}$
Junction-to-Ambient Thermal Resistance	$R_{\theta JA}$	62.5	$^\circ\text{C/W}$

COMPANY RESERVES THE RIGHT TO IMPROVE PRODUCT DESIGN 、FUNCTIONS AND RELIABILITY WITHOUT NOTICE

Electrical Characteristics ($T_C=25$, Unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Units
Static						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V$ 、 $I_D=250\mu A$	55	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ 、 $I_D=250\mu A$	1	1.6	3	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=10V$ 、 $I_D=30A$	-	4.2	5.5	$m\Omega$
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=44V$ 、 $V_{GS}=0V$	-	-	1	μA
Gate Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20V$ 、 $V_{DS}=0V$	-	-	100	nA
Dynamic						
Total Gate Charge	Qg	$V_{DS}=30V$ 、 $I_D=30A$ $V_{GS}=10V$	-	98	-	nC
Gate-Source Charge	Qgs		-	37.6	-	
Gate-Drain Charge	Qgd		-	26.2	-	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD}=30V$ 、 $I_D=30A$ $V_{GS}=10V$ 、 $R_G=3.6\Omega$	-	21.8	-	ns
Turn-On Rise Time	t_r		-	12.6	-	
Turn-Off Delay Time	$t_{d(off)}$		-	68	-	
Turn-Off Fall Time	t_f		-	58	-	
Input Capacitance	C_{iss}	$V_{DS}=30V$ 、 $V_{GS}=0V$ $f=1.0MHz$	-	4150	-	pF
Output Capacitance	C_{oss}		-	385	-	
Reverse Transfer Capacitance	C_{rss}		-	260	-	
Gate Resistance	Rg		-	1.3	-	Ω
Source-Drain Diode						
Max. Diode Forward Voltage	I_S	-	-	-	110	A
Diode Forward Voltage	V_{SD}	$I_S=30A$ 、 $V_{GS}=0V$	-	0.85	1.4	V
Reverse Recovery Time	t_{rr}	$V_{GS}=0V$ 、 $I_S=30A$ $di/dt=100A/\mu s$	-	52	-	ns
Reverse Recovery Charge	Q_{rr}		-	128	-	μC

NOTE : Pulse Test : Pulse Width $\leq 300\mu s$, duty cycle $\leq 2\%$

Typical Characteristics Curves ($T_C=25^{\circ}\text{C}$, unless otherwise noted)

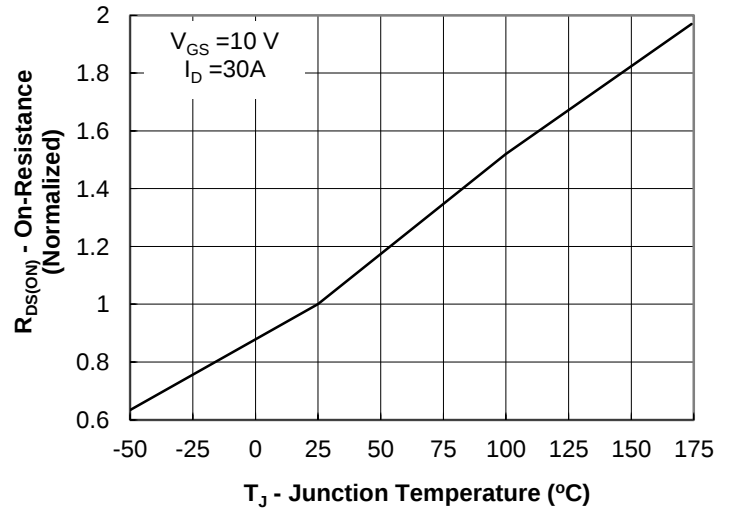
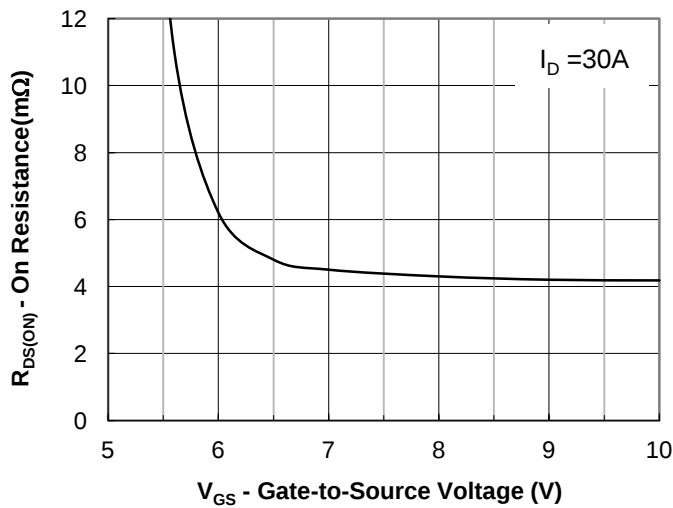
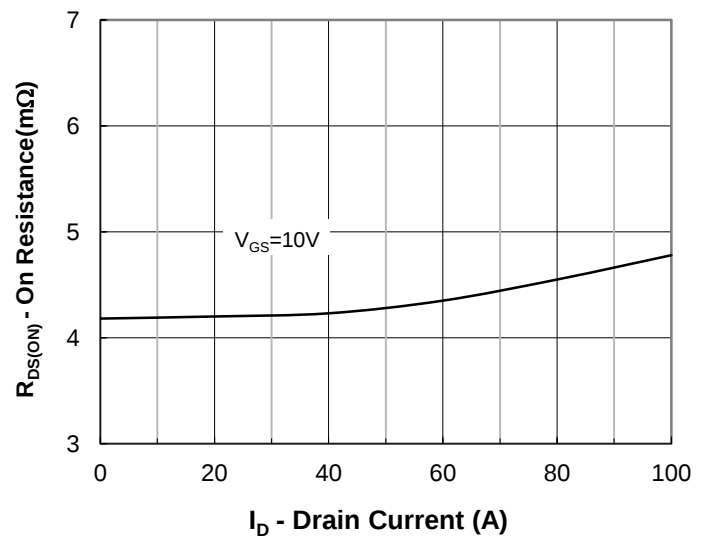
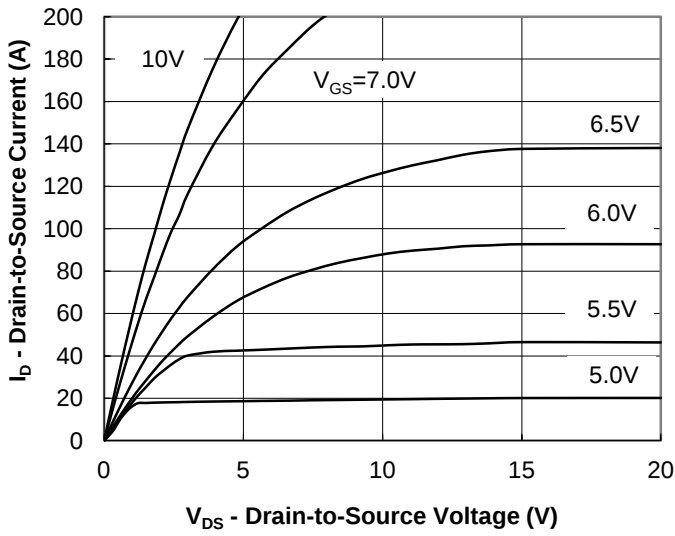
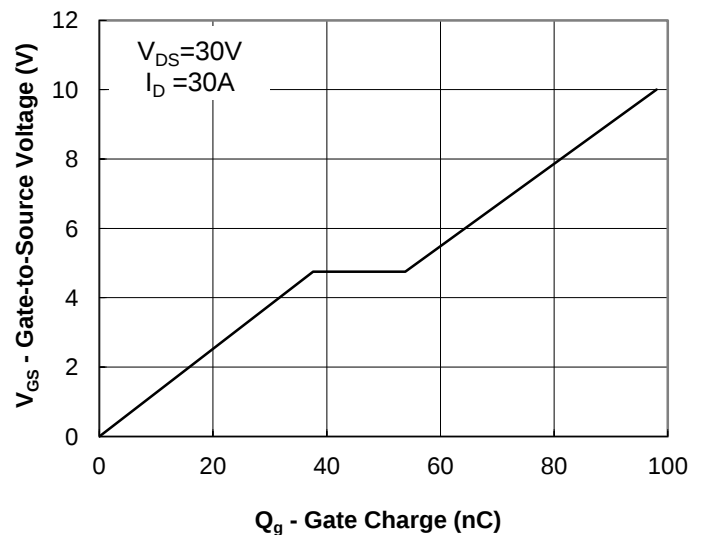
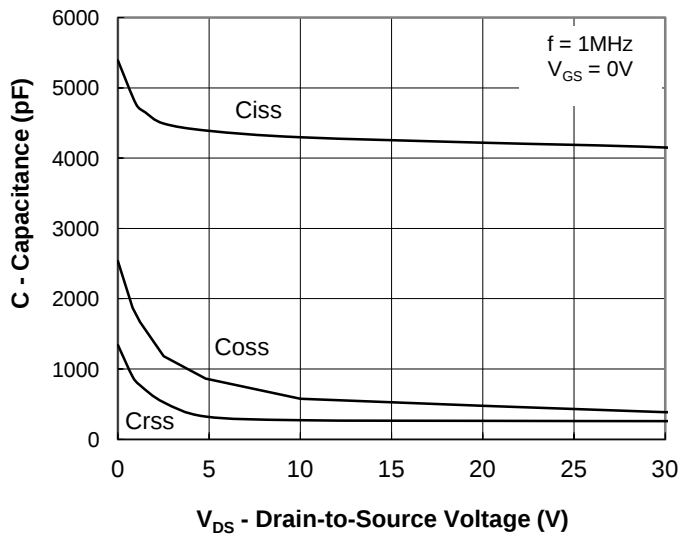


Fig.3 On-Resistance vs Gate to Source Voltage

Fig.4 On-Resistance vs Junction Temperature



Typical Characteristics Curves ($T_C=25^{\circ}\text{C}$, unless otherwise noted)

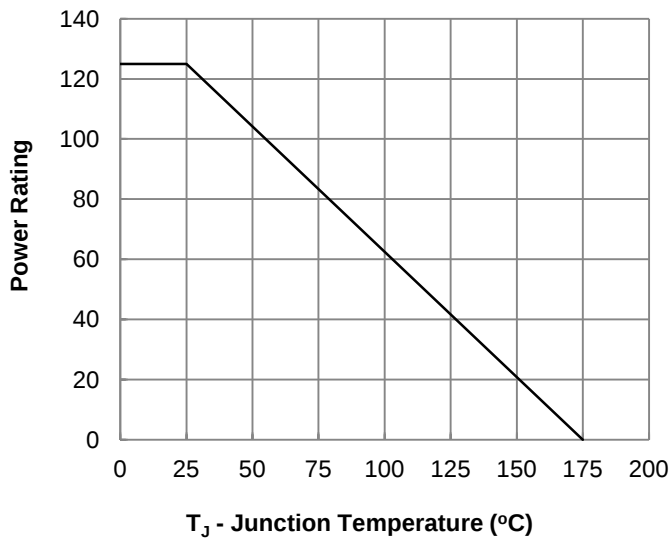


Fig.7 Power Derating Curve

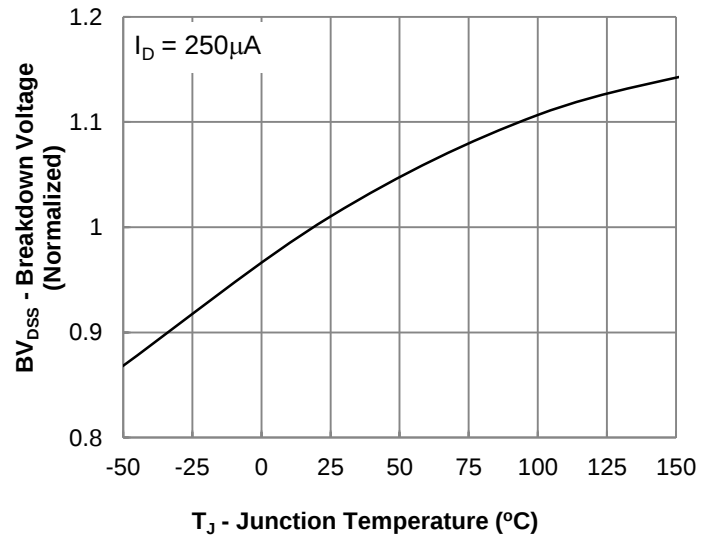


Fig.8 Breakdown Voltage vs Junction Temperature

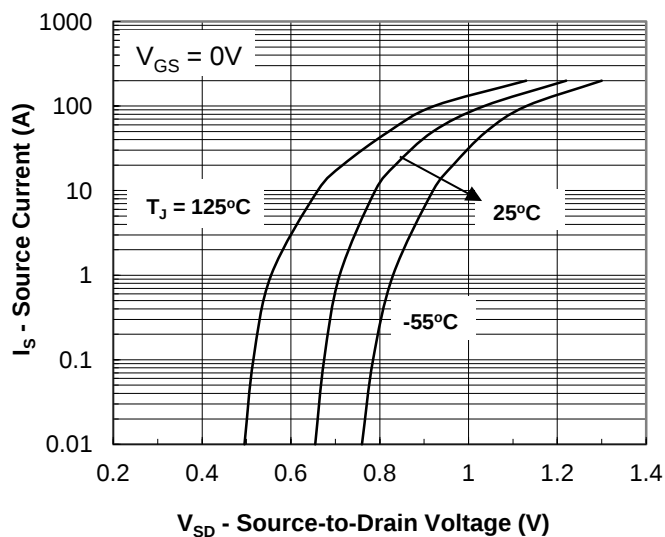


Fig.9 Body Diode Forward Voltage Characteristic